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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, LINbus, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	80
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D - 16bit; D/A - 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl26z256vll4

Security and integrity modules

- 80-bit unique identification number per chip

Ordering Information [1]

Part Number	Memory		Maximum number of I\O's
	Flash (KB)	SRAM (KB)	
MKL26Z256VLH4	256	32	50
MKL26Z256VMP4	256	32	50
MKL26Z128VLL4	128	16	80
MKL26Z256VLL4	256	32	80
MKL26Z128VMC4	128	16	84
MKL26Z256VMC4	256	32	84

1. To confirm current availability of ordererable part numbers, go to http://www.freescale.com and perform a part number search.

Related Resources

Type	Description	Resource
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	Solution Advisor
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KL26P121M48SF4RM[1]
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	KL26P121M48SF4[1]
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	KINETIS_L_*x*N40H[2]
Package drawing	Package dimensions are provided in package drawings.	LQFP 64-pin: 98ASS23234W[1] MAPBGA 64-pin: 98ASA00420D[1] LQFP 100-pin: 98ASS23308W[1] MAPBGA 121-pin: 98ASA00344D[1]

1. To find the associated resource, go to http://www.freescale.com and perform a search using this term.
2. To find the associated resource, go to http://www.freescale.com and perform a search using this term with the "*x*" replaced by the revision of the device you are using.

1 Ratings

1.1 Thermal handling ratings

Table 1. Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.2 Moisture handling ratings

Table 2. Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.3 ESD handling ratings

Table 3. ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	–2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	–500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105 °C	–100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

1.4 Voltage and current operating ratings

Table 4. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	IO pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{USB_DP}	USB_DP input voltage	–0.3	3.63	V
V_{USB_DM}	USB_DM input voltage	–0.3	3.63	V
V_{REGIN}	USB regulator input	–0.3	6.0	V

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

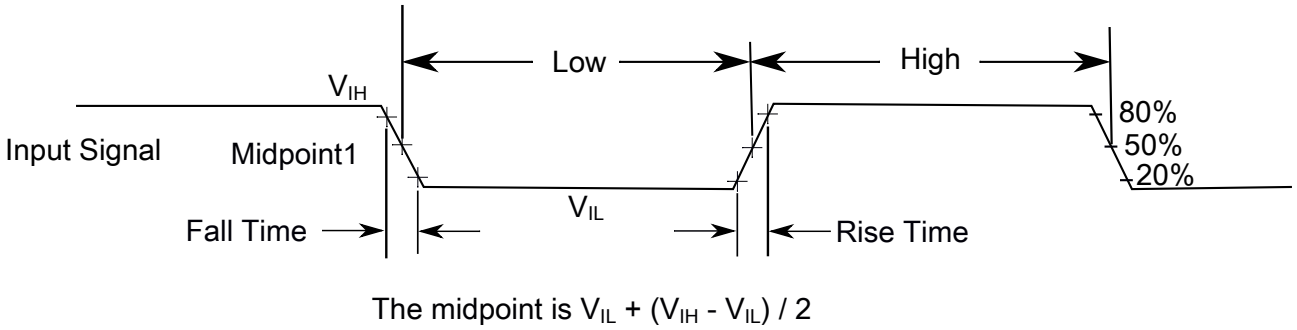


Figure 2. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength

Table 6. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	—
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV = 00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV = 01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV = 10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	—
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	—
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV = 00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV = 01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV = 10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	—
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	—
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	µs	—

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors

Table 7. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — Normal drive pad (except RESET_b)				1, 2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -5 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -2.5 mA	V_{DD} – 0.5	—	V	
V_{OH}	Output high voltage — High drive pad (except RESET_b)				1, 2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -20 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -10 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	

Table continues on the next page...

Table 10. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I_{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	µA
I_{ADC}	ADC peripheral adder combining the measured values at V_{DD} and V_{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	µA

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

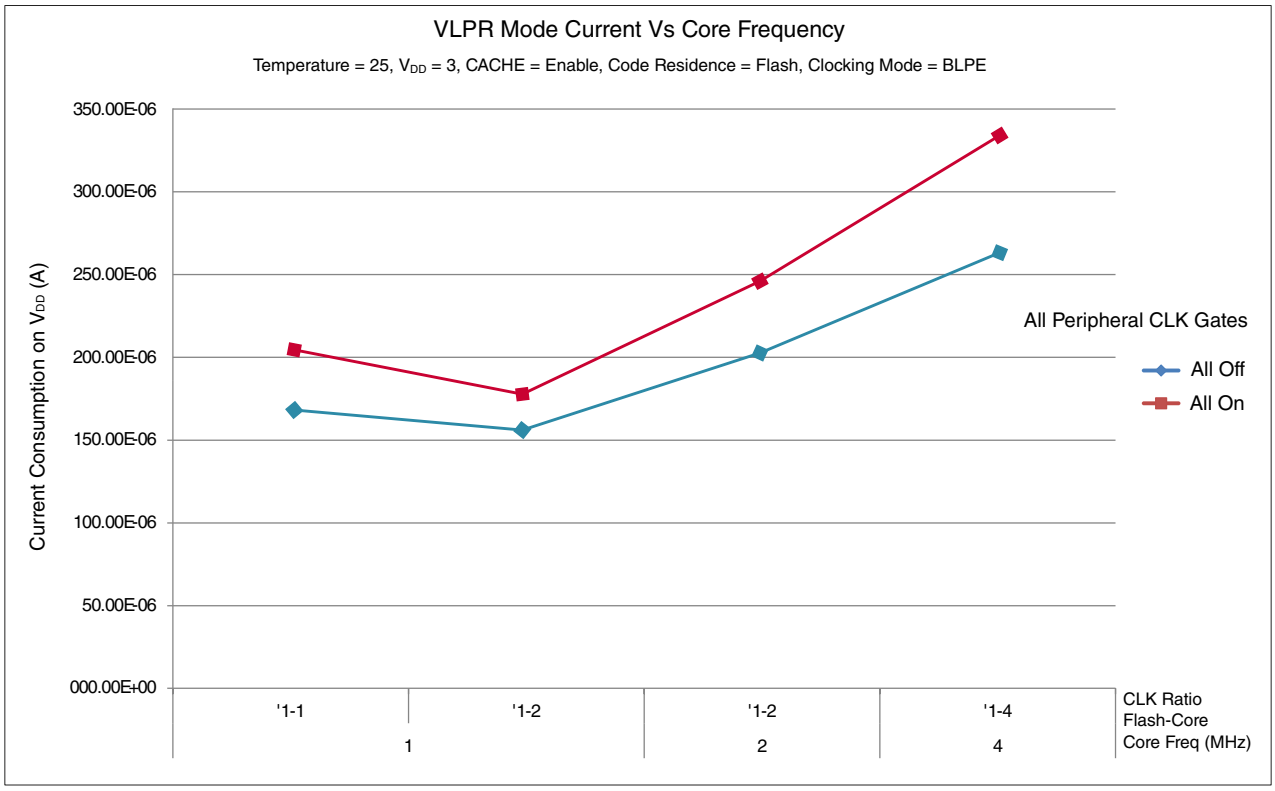


Figure 4. VLPR mode current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 11. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	12	dBµV	1,2
V_{RE2}	Radiated emissions voltage, band 2	50–150	8	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	7	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	4	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	M	—	2,3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 8 MHz (crystal), f_{SYS} = 48 MHz, f_{BUS} = 24 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

2.4.2 Thermal attributes

Table 16. Thermal attributes

Board type	Symbol	Description	121 MAPBGA	100 LQFP	64 LQFP	64 MAPBGA	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	94	64	69	49.8	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	57	51	51	42.3	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	81	54	58	40.9	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	53	45	44	37.7	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	40	37	33	39.2	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	30	19	19	50.3	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	8	4	4	2.2	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

3 Peripheral operating requirements and behaviors

3.1 Core modules

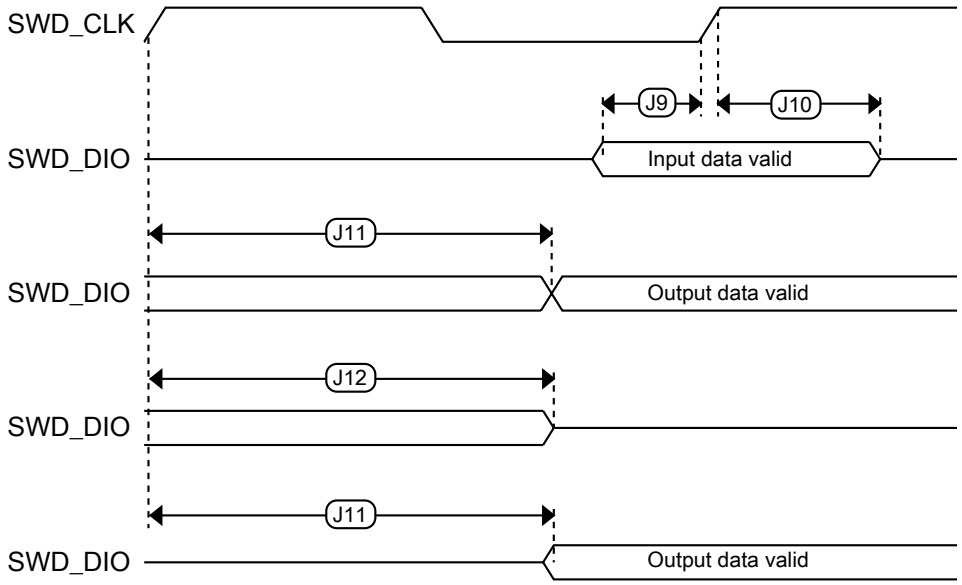


Figure 6. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 18. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal V_{DD} and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using C3[SCTRIM] and C4[SCFTRIM]	—	± 0.3	± 0.6	$\%f_{dco}$	1

Table continues on the next page...

Table 19. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• 24 MHz • 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	µA	
	• 4 MHz	—	400	—	µA	
	• 8 MHz (RANGE=01)	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 21. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	µs	—
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	52	452	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 22. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk128k}$	Read 1s Block execution time • 128 KB program flash	—	—	1.7	ms	—
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	µs	1
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1
t_{pgm4}	Program Longword execution time	—	65	145	µs	—
$t_{ersblk128k}$	Erase Flash Block execution time • 128 KB program flash	—	88	600	ms	2
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	—
t_{rdonce}	Read Once execution time	—	—	25	µs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	µs	—
t_{ersall}	Erase All Blocks execution time	—	175	1300	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.6.1.1 16-bit ADC operating conditions

Table 25. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	—
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} - V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage	• 16-bit differential mode • All other modes	VREFL VREFL	— —	31/32 * VREFH VREFH	V	—
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	—
R_{ADIN}	Input series resistance		—	2	5	kΩ	—
R_{AS}	Analog source resistance (external)	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

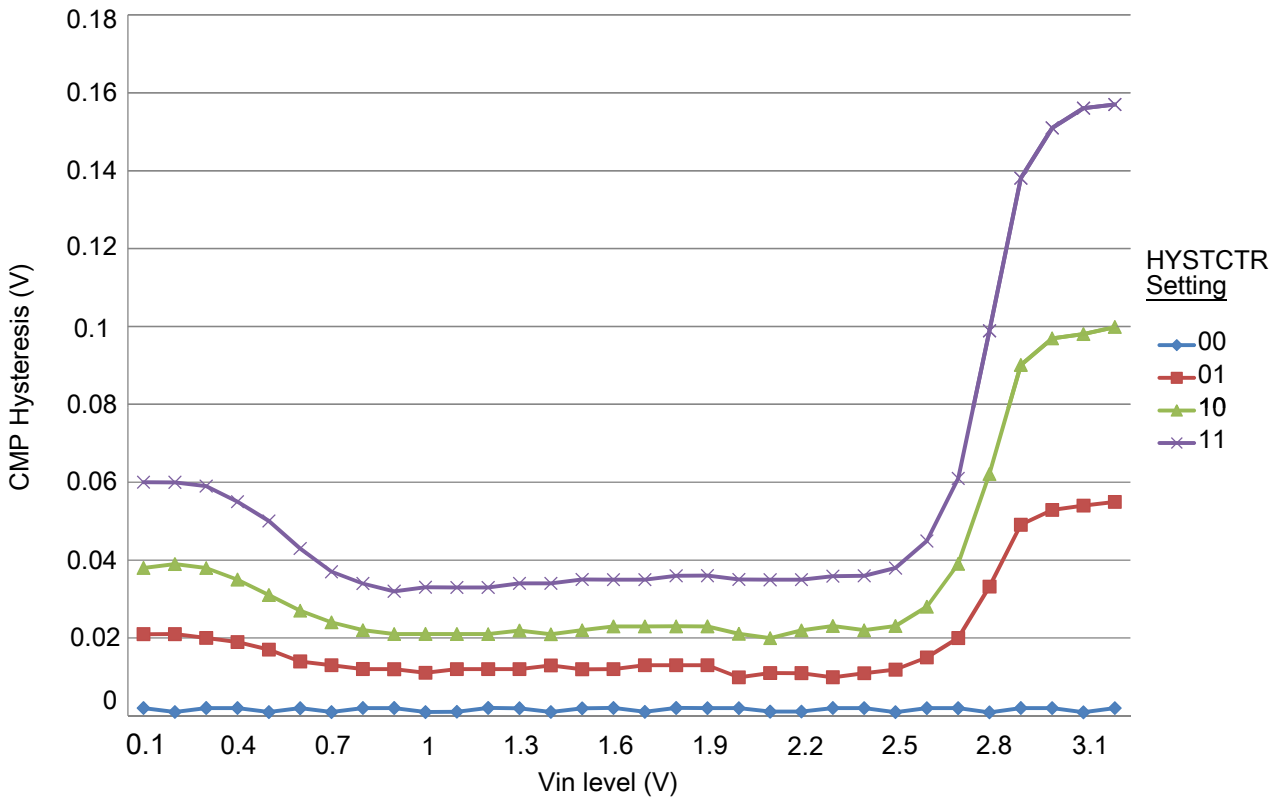


Figure 11. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

3.6.3.1 12-bit DAC operating requirements

Table 28. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH}.
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

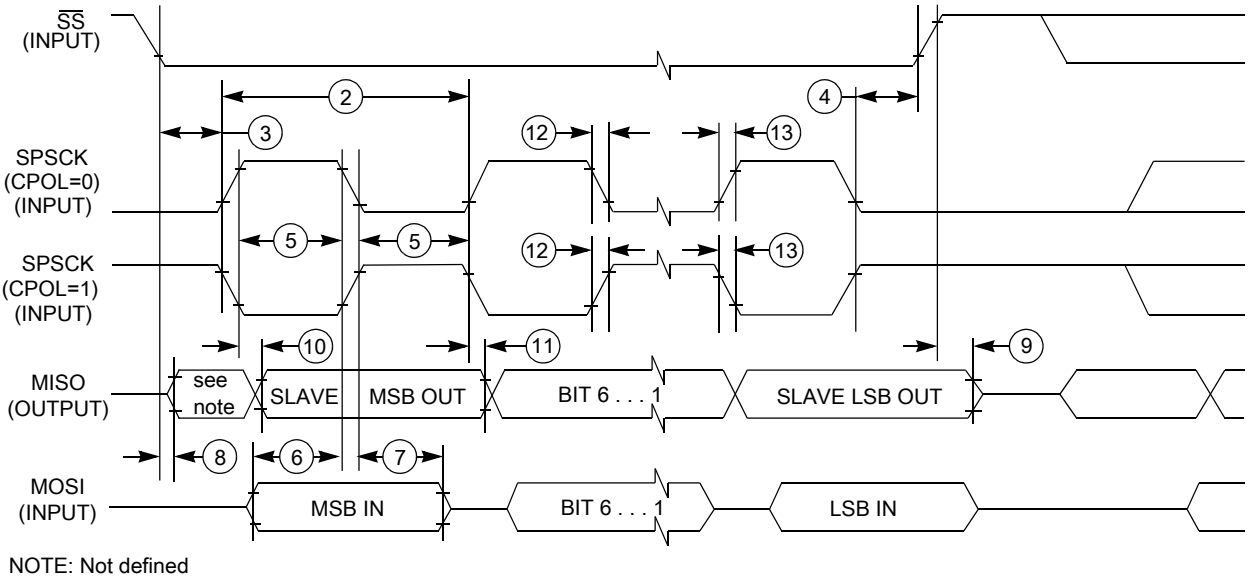


Figure 17. SPI slave mode timing (CPHA = 1)

3.8.4 Inter-Integrated Circuit Interface (I2C) timing

Table 35. I2C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f_{SCL}	0	100	0	400[1]	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	4	—	0.6	—	µs
LOW period of the SCL clock	t_{LOW}	4.7	—	1.3	—	µs
HIGH period of the SCL clock	t_{HIGH}	4	—	0.6	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	4.7	—	0.6	—	µs
Data hold time for I^2C bus devices	t_{HD}; DAT	0[2]	3.45[3]	0[4]	0.9[2]	µs
Data set-up time	t_{SU}; DAT	250[5]	—	100[3, 6]	—	ns
Rise time of SDA and SCL signals	t_r	—	1000	20 +0.1C_b[7]	300	ns
Fall time of SDA and SCL signals	t_f	—	300	20 +0.1C_b[6]	300	ns
Set-up time for STOP condition	t_{SU}; STO	4	—	0.6	—	µs
Bus free time between STOP and START condition	t_{BUF}	4.7	—	1.3	—	µs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	N/A	N/A	0	50	ns

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only achieved when using the High drive pins (see Voltage and current operating behaviors) or when using the Normal drive pins and VDD ≥ 2.7 V

121 BGA	100 LQFP	64 BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
E4	1	A1	1	PTE0	DISABLED		PTE0	SPI1_MISO	UART1_TX	RTC_ CLKOUT	CMP0_OUT	I2C1_SDA	
E3	2	B1	2	PTE1	DISABLED		PTE1	SPI1_MOSI	UART1_RX		SPI1_MISO	I2C1_SCL	
E2	3	—	—	PTE2	DISABLED		PTE2	SPI1_SCK					
F4	4	—	—	PTE3	DISABLED		PTE3	SPI1_MISO			SPI1_MOSI		
H7	5	—	—	PTE4	DISABLED		PTE4	SPI1_PCS0					
G4	6	—	—	PTE5	DISABLED		PTE5						
F3	7	—	—	PTE6	DISABLED		PTE6			I2S0_MCLK	audioUSB_ SOF_OUT		
E6	8	—	3	VDD	VDD	VDD							
G7	9	C4	4	VSS	VSS	VSS							
L6	—	—	—	VSS	VSS	VSS							
F1	10	E1	5	USB0_DP	USB0_DP	USB0_DP							
F2	11	D1	6	USB0_DM	USB0_DM	USB0_DM							
G1	12	E2	7	VOUT33	VOUT33	VOUT33							
G2	13	D2	8	VREGIN	VREGIN	VREGIN							
H1	14	—	—	PTE16	ADC0_DP1/ ADC0_SE1	ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_ CLKIN0			
H2	15	—	—	PTE17	ADC0_DM1/ ADC0_SE5a	ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_ CLKIN1		LPTMR0_ ALT3	
J1	16	—	—	PTE18	ADC0_DP2/ ADC0_SE2	ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO		
J2	17	—	—	PTE19	ADC0_DM2/ ADC0_SE6a	ADC0_DM2/ ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI		
K1	18	G1	9	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	UART0_TX			
K2	19	F1	10	PTE21	ADC0_DM0/ ADC0_SE4a	ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	UART0_RX			
L1	20	G2	11	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX			
L2	21	F2	12	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX			
F5	22	F4	13	VDDA	VDDA	VDDA							
G5	23	G4	14	VREFH	VREFH	VREFH							
G6	24	G3	15	VREFL	VREFL	VREFL							
F6	25	F3	16	VSSA	VSSA	VSSA							
L3	26	H1	17	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_ CLKIN0			
K5	27	H2	18	PTE30	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_ CLKIN1			
L4	28	H3	19	PTE31	DISABLED		PTE31		TPM0_CH4				
L5	29	—	—	VSS	VSS	VSS							

121 BGA	100 LQFP	64 BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
K6	30	—	—	VDD	VDD	VDD							
H5	31	H4	20	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
J5	32	H5	21	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
H6	33	—	—	PTE26	DISABLED		PTE26		TPM0_CH5			RTC_ CLKOUT	USB_CLKIN
J6	34	D3	22	PTA0	SWD_CLK	TSI0_CH1	PTA0		TPM0_CH5				SWD_CLK
H8	35	D4	23	PTA1	DISABLED	TSI0_CH2	PTA1	UART0_RX	TPM2_CH0				
J7	36	E5	24	PTA2	DISABLED	TSI0_CH3	PTA2	UART0_TX	TPM2_CH1				
H9	37	D5	25	PTA3	SWD_DIO	TSI0_CH4	PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
J8	38	G5	26	PTA4	NMI_b	TSI0_CH5	PTA4	I2C1_SDA	TPM0_CH1				NMI_b
K7	39	F5	27	PTA5	DISABLED		PTA5	USB_CLKIN	TPM0_CH2			I2S0_TX_ BCLK	
E5	—	—	—	VDD	VDD	VDD							
G3	—	—	—	VSS	VSS	VSS							
K3	40	—	—	PTA6	DISABLED		PTA6		TPM0_CH3				
H4	41	—	—	PTA7	DISABLED		PTA7		TPM0_CH4				
K8	42	H6	28	PTA12	DISABLED		PTA12		TPM1_CH0			I2S0_TXD0	
L8	43	G6	29	PTA13	DISABLED		PTA13		TPM1_CH1			I2S0_TX_FS	
K9	44	—	—	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_RX_ BCLK	I2S0_TXD0
L9	45	—	—	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0	
J10	46	—	—	PTA16	DISABLED		PTA16	SPI0_MOSI			SPI0_MISO	I2S0_RX_FS	I2S0_RXD0
H10	47	—	—	PTA17	DISABLED		PTA17	SPI0_MISO			SPI0_MOSI	I2S0_MCLK	
L10	48	G7	30	VDD	VDD	VDD							
K10	49	H7	31	VSS	VSS	VSS							
L11	50	H8	32	PTA18	EXTAL0	EXTAL0	PTA18		UART1_RX	TPM_ CLKIN0			
K11	51	G8	33	PTA19	XTAL0	XTAL0	PTA19		UART1_TX	TPM_ CLKIN1		LPTMR0_ ALT1	
J11	52	F8	34	PTA20	RESET_b		PTA20						RESET_b
G11	53	F7	35	PTB0/ LLWU_P5	ADC0_SE8/ TSI0_CH0	ADC0_SE8/ TSI0_CH0	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0				
G10	54	F6	36	PTB1	ADC0_SE9/ TSI0_CH6	ADC0_SE9/ TSI0_CH6	PTB1	I2C0_SDA	TPM1_CH1				
G9	55	E7	37	PTB2	ADC0_SE12/ TSI0_CH7	ADC0_SE12/ TSI0_CH7	PTB2	I2C0_SCL	TPM2_CH0				
G8	56	E8	38	PTB3	ADC0_SE13/ TSI0_CH8	ADC0_SE13/ TSI0_CH8	PTB3	I2C0_SDA	TPM2_CH1				
E11	57	—	—	PTB7	DISABLED		PTB7						
D11	58	—	—	PTB8	DISABLED		PTB8	SPI1_PCS0	EXTRG_IN				
E10	59	—	—	PTB9	DISABLED		PTB9	SPI1_SCK					
D10	60	—	—	PTB10	DISABLED		PTB10	SPI1_PCS0					

	1	2	3	4	5	6	7	8	9	10	11	
A	PTD7	PTD5	PTD4/ LLWU_P14	NC	NC	PTC13	PTC8	PTC4/ LLWU_P8	PTC21	PTC20	NC	A
B	NC	PTD6/ LLWU_P15	PTD3	PTC18	NC	PTC12	PTC7	PTC3/ LLWU_P7	PTC0	PTB16	PTC22	B
C	NC	NC	PTD2	PTC17	PTC11	PTC10	PTC6/ LLWU_P10	PTC2	PTB19	PTB11	PTC23	C
D	NC	NC	PTD1	PTD0	PTC16	PTC9	PTC5/ LLWU_P9	PTC1/ LLWU_P6/ RTC_CLKIN	PTB18	PTB10	PTB8	D
E	NC	PTE2	PTE1	PTE0	VDD	VDD	VDD	PTB23	PTB17	PTB9	PTB7	E
F	USB0_DP	USB0_DM	PTE6	PTE3	VDDA	VSSA	VSS	PTB22	PTB21	PTB20	NC	F
G	VOUT33	VREGIN	VSS	PTE5	VREFH	VREFL	VSS	PTB3	PTB2	PTB1	PTB0/ LLWU_P5	G
H	PTE16	PTE17	NC	PTA7	PTE24	PTE26	PTE4	PTA1	PTA3	PTA17	NC	H
J	PTE18	PTE19	NC	NC	PTE25	PTA0	PTA2	PTA4	NC	PTA16	PTA20	J
K	PTE20	PTE21	PTA6	NC	PTE30	VDD	PTA5	PTA12	PTA14	VSS	PTA19	K
L	PTE22	PTE23	PTE29	PTE31	VSS	VSS	NC	PTA13	PTA15	VDD	PTA18	L
	1	2	3	4	5	6	7	8	9	10	11	

Figure 23. KL26 121-pin BGA pinout diagram

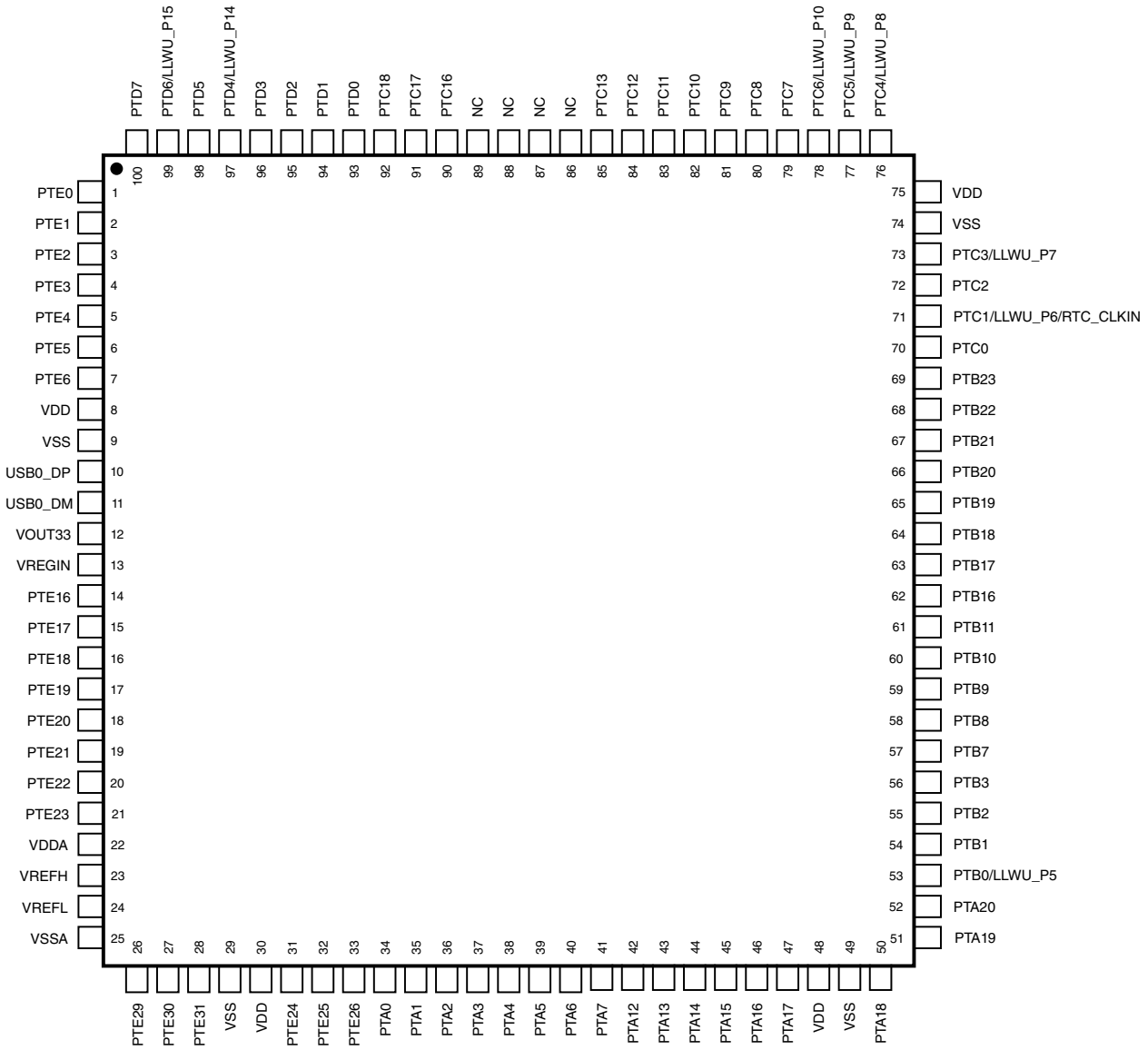


Figure 24. KL26 100-pin LQFP pinout diagram

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Table 41. Part number fields descriptions

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
KL##	Kinetis family	• KL26
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	• 128 = 128 KB • 256 = 256 KB
R	Silicon revision	• (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LL = 100 LQFP (14 mm x 14 mm) • MC = 121 MAPBGA (8 mm x 8 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz
N	Packaging type	• R = Tape and reel

7.4 Example

This is an example part number:

MKL26Z256VLH4

8.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

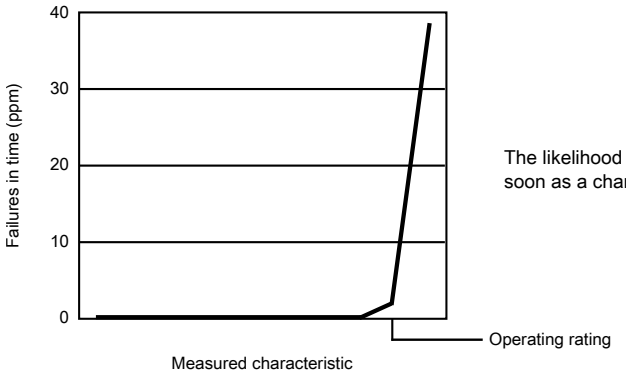
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

8.4.1 Example

This is an example of an operating rating:

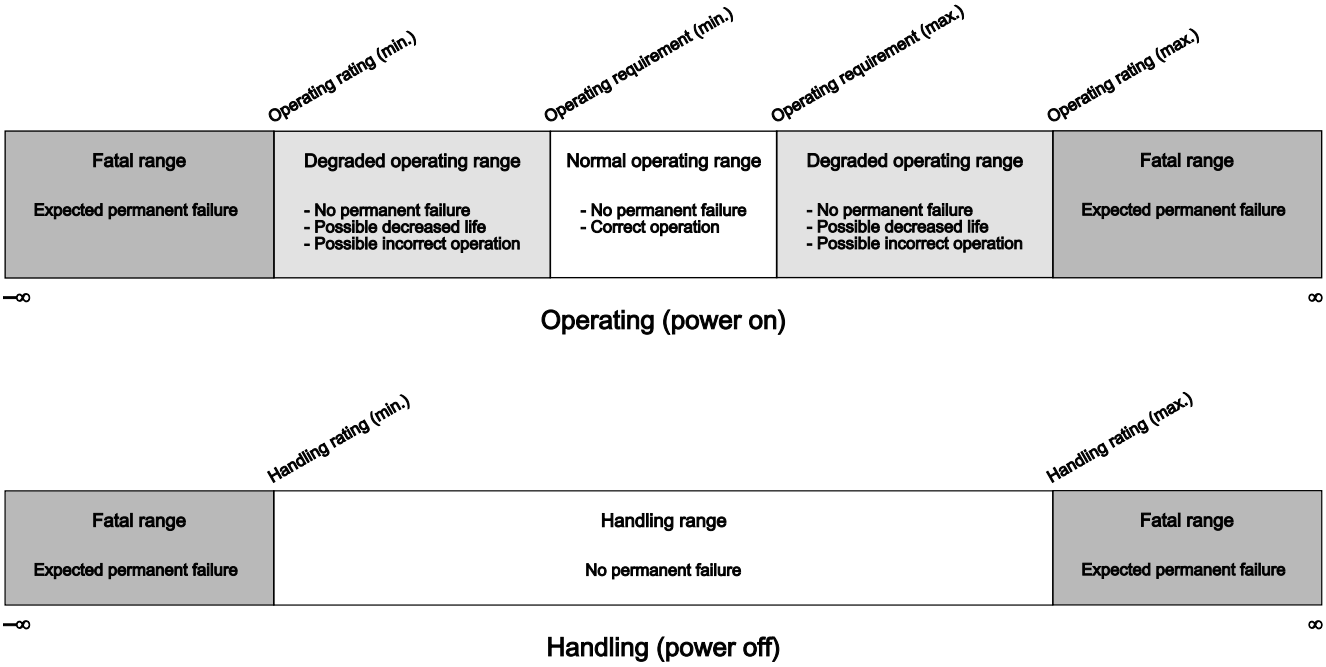
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

8.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

8.6 Relationship between ratings and operating requirements



8.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

8.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.